SKMT 92, SKKL 92

SEMIPACK® 1

Thyristor / Diode Modules

SKMT 92, SKKL 92

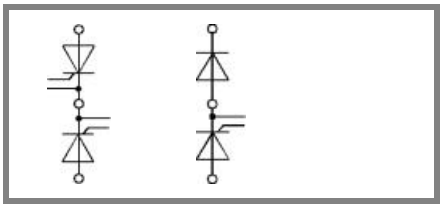
Features

- Heat transfer through aluminium oxide ceramic isolated metal baseplate
- Hard soldered joints for high reliability
- UL recognized, file no. E 63 532

Typical Applications

- Line rectifiers for transistorized AC motor controllers (SKKL)
- DC braking of AC motor (SKMT)

1) See the assembly instructions



SKMT SKKL

V_{RSM} V	V_{RRM}, V_{DRM} V	I_{TRMS} = 150 A (maximum value for continuous operation) I_{TAV} = 95 A (sin. 180; T_c = 85 °C)		
900	800	SKMT 92/08E		
1300	1200		SKKL 92/12E	
1500	1400	SKMT 92/14E		
1700	1600	SKMT 92/16E	SKKL 92/16E	
1900	1800	SKMT 92/18E		

Symbol	Conditions	Values	Units
I_{TAV}	sin. 180; T_c = 85 (100) °C	95 (68)	A
I_D	P3/180; T_a = 45 °C; B2 / B6	70 / 85	A
	P3/180F; T_a = 35 °C; B2 / B6	140 /175	A
I_{RMS}	P3/180F; T_a = 35 °C; W1 / W3	190 / 3 * 135	A
I_{TSM}	T_{vj} = 25 °C; 10 ms	2000	A
	T_{vj} = 125 °C; 10 ms	1750	A
i^2t	T_{vj} = 25 °C; 8,3 ... 10 ms	20000	A^2s
	T_{vj} = 125 °C; 8,3 ... 10 ms	15000	A^2s
V_T	T_{vj} = 25 °C; I_T = 300 A	max. 1,65	V
$V_{T(TO)}$	T_{vj} = 125 °C	0,9	V
r_T	T_{vj} = 125 °C	2	mΩ
I_{DD}; I_{RD}	T_{vj} = 125 °C; V_{RD} = V_{RRM}; V_{DD} = V_{DRM}	max. 20	mA
t_{gd}	T_{vj} = 25 °C; I_G = 1 A; di_G/dt = 1 A/µs	1	µs
t_{gr}	V_D = 0,67 * V_{DRM}	2	µs
$(di/dt)_{cr}$	T_{vj} = 125 °C	max. 150	A/µs
$(dv/dt)_{cr}$	T_{vj} = 125 °C	max. 1000	V/µs
t_q	T_{vj} = 125 °C	100	µs
I_H	T_{vj} = 25 °C; typ. / max.	150 / 250	mA
I_L	T_{vj} = 25 °C; R_G = 33 Ω; typ. / max.	300 / 600	mA
V_{GT}	T_{vj} = 25 °C; d.c.	min. 3	V
I_{GT}	T_{vj} = 25 °C; d.c.	min. 150	mA
V_{GD}	T_{vj} = 125 °C; d.c.	max. 0,25	V
I_{GD}	T_{vj} = 125 °C; d.c.	max. 6	mA
$R_{th(j-c)}$	cont.; per thyristor / per module	0,28 / 0,14	K/W
$R_{th(j-c)}$	sin. 180; per thyristor / per module	0,3 / 0,15	K/W
$R_{th(j-c)}$	rec. 120; per thyristor / per module	0,32 / 0,16	K/W
$R_{th(c-s)}$	per thyristor / per module	0,2 / 0,1	K/W
T_{vj}		- 40 ... + 125	°C
T_{stg}		- 40 ... + 125	°C
V_{isol}	a. c. 50 Hz; r.m.s.; 1 s / 1 min.	3600 / 3000	V~
M_s	to heatsink	5 ± 15 %[1)]	Nm
M_t	to terminals	3 ± 15 %	Nm
a		5 * 9,81	m/s^2
m	approx.	95	g
Case	SKMT	A 72	
	SKKL	A 59	

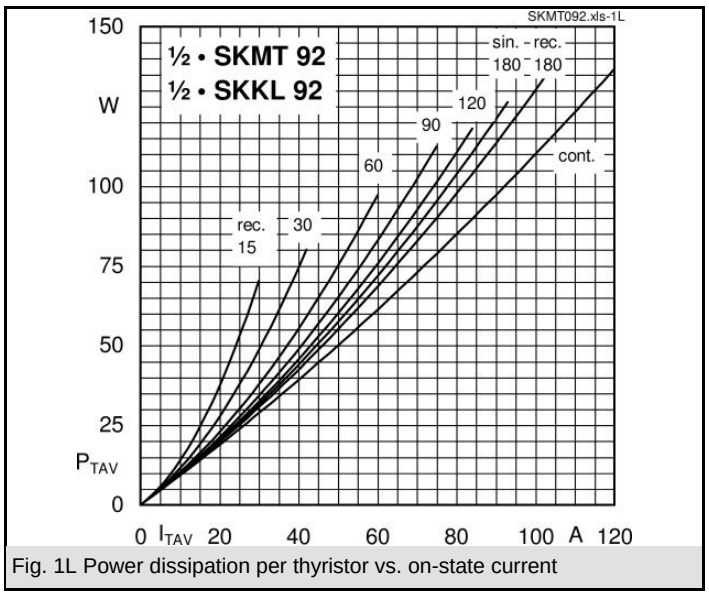


Fig. 1L Power dissipation per thyristor vs. on-state current

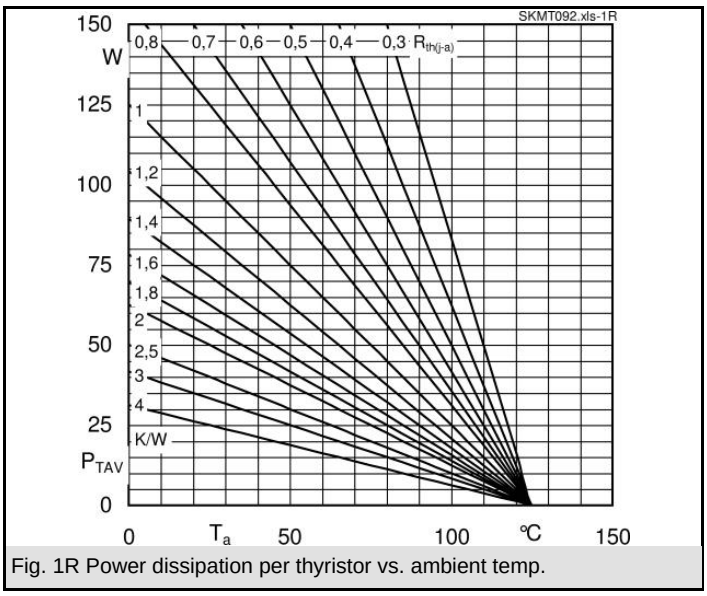


Fig. 1R Power dissipation per thyristor vs. ambient temp.

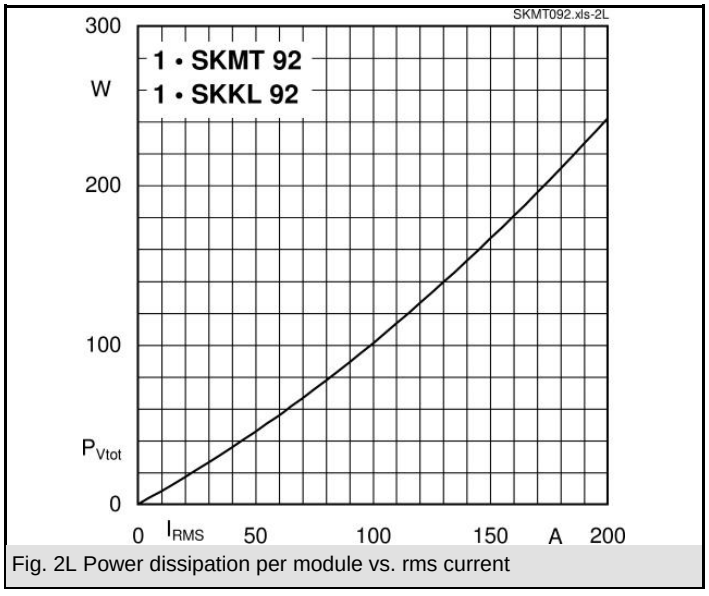


Fig. 2L Power dissipation per module vs. rms current

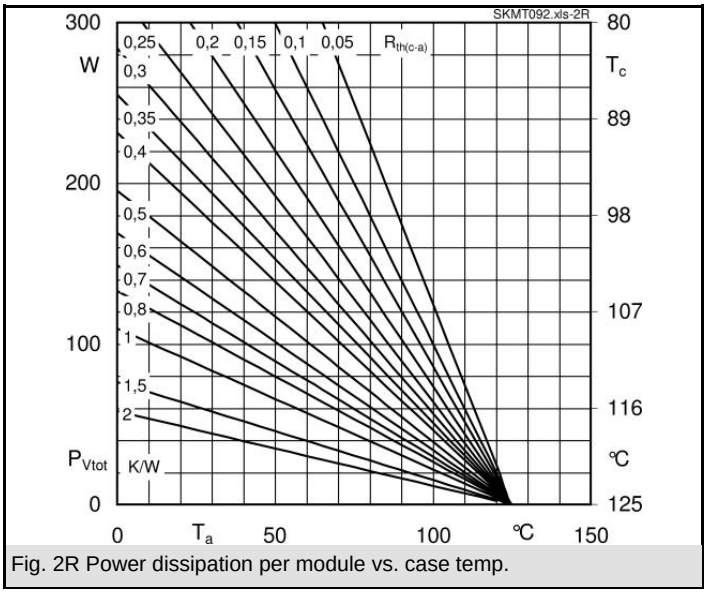


Fig. 2R Power dissipation per module vs. case temp.

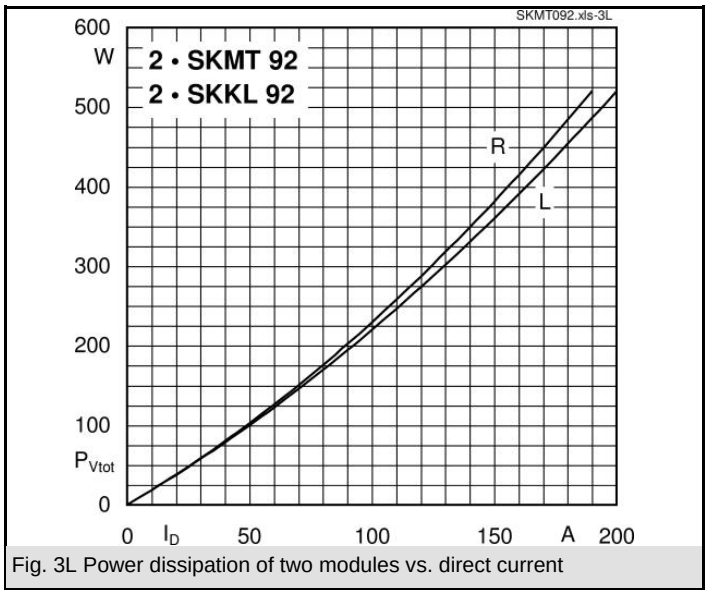


Fig. 3L Power dissipation of two modules vs. direct current

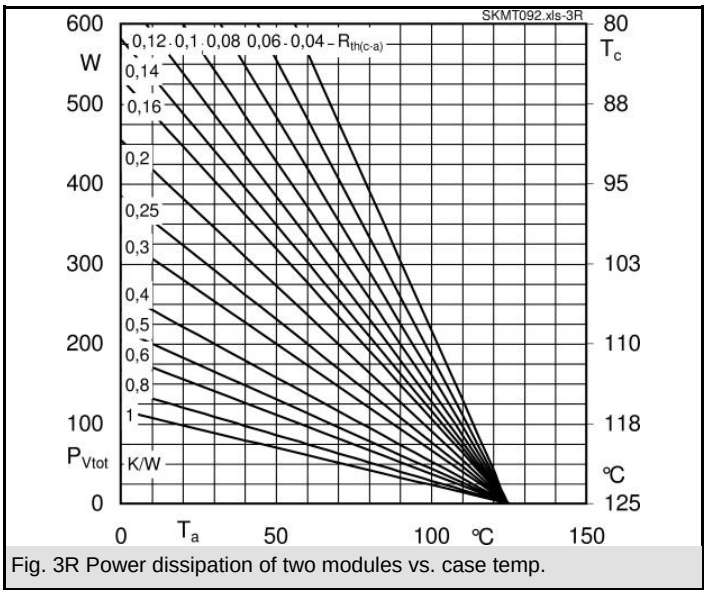


Fig. 3R Power dissipation of two modules vs. case temp.

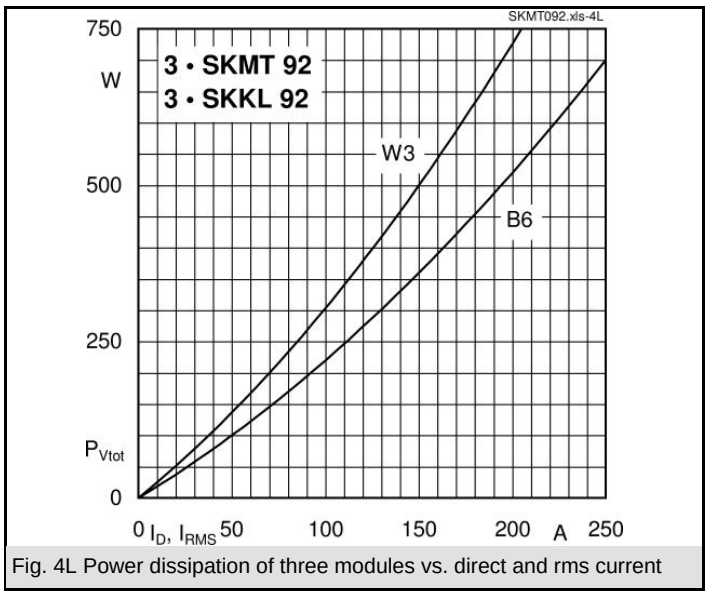


Fig. 4L Power dissipation of three modules vs. direct and rms current

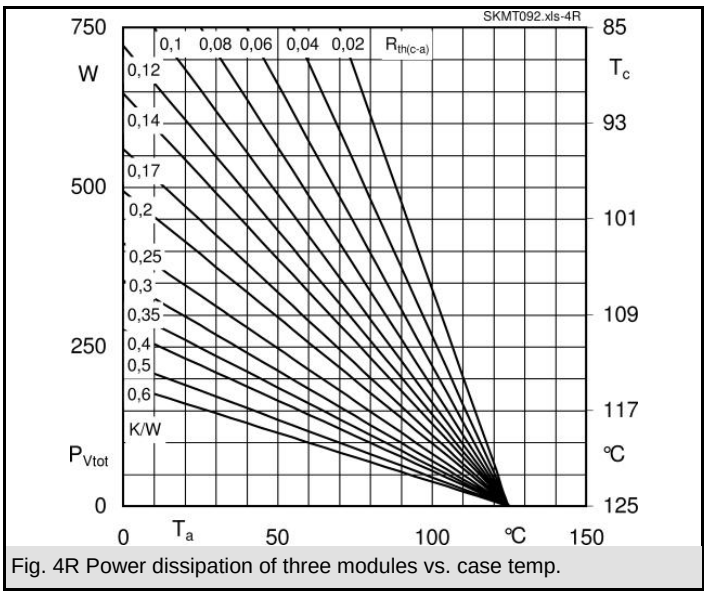


Fig. 4R Power dissipation of three modules vs. case temp.

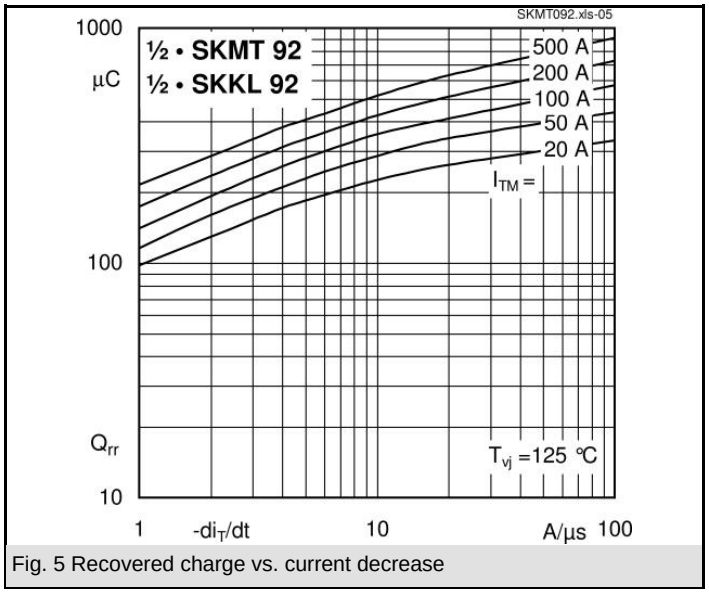


Fig. 5 Recovered charge vs. current decrease

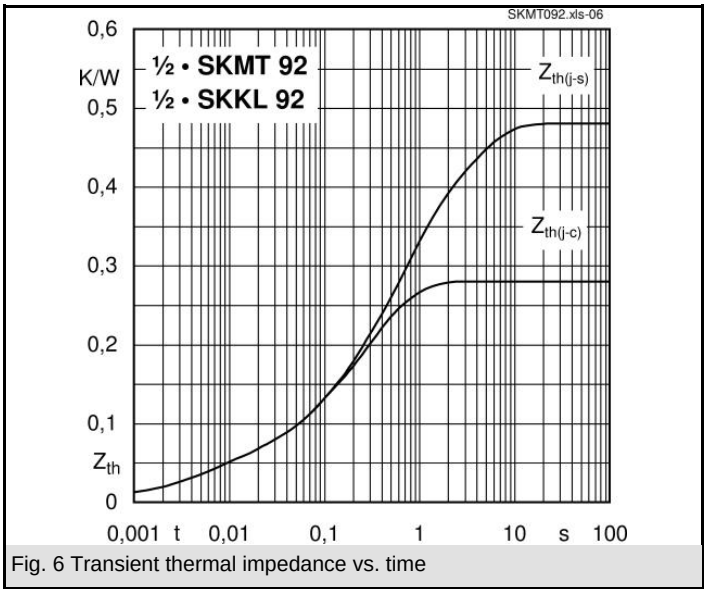


Fig. 6 Transient thermal impedance vs. time

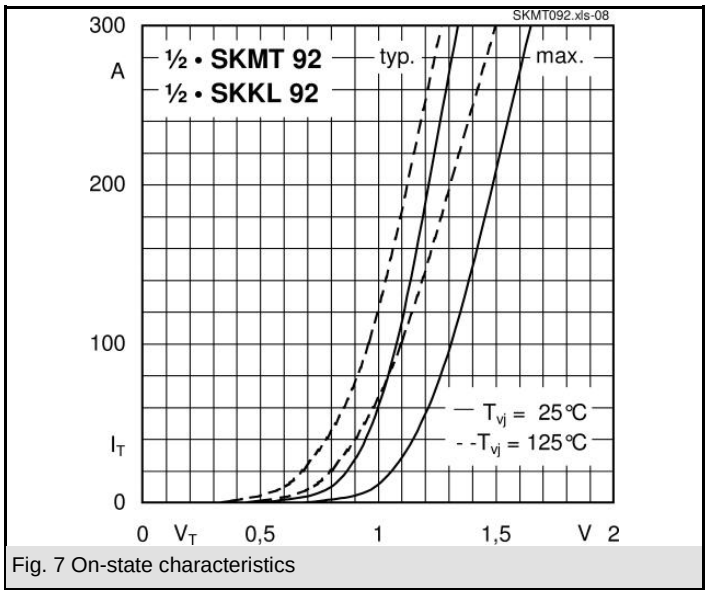


Fig. 7 On-state characteristics

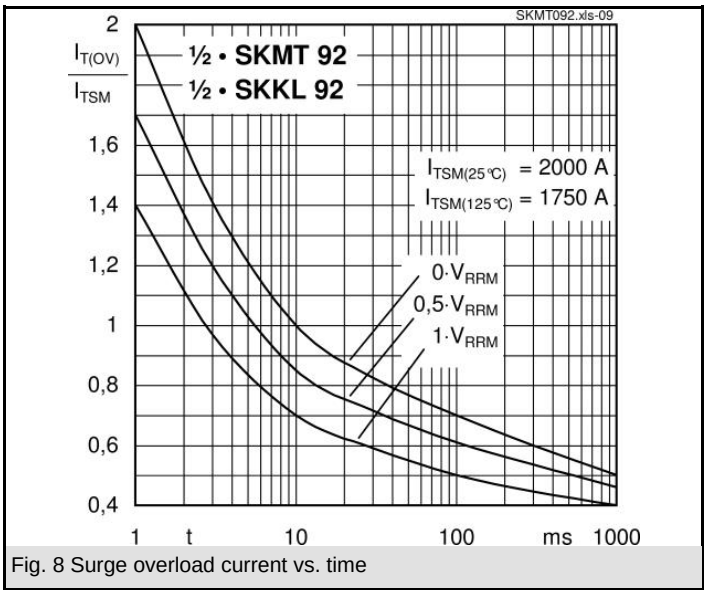
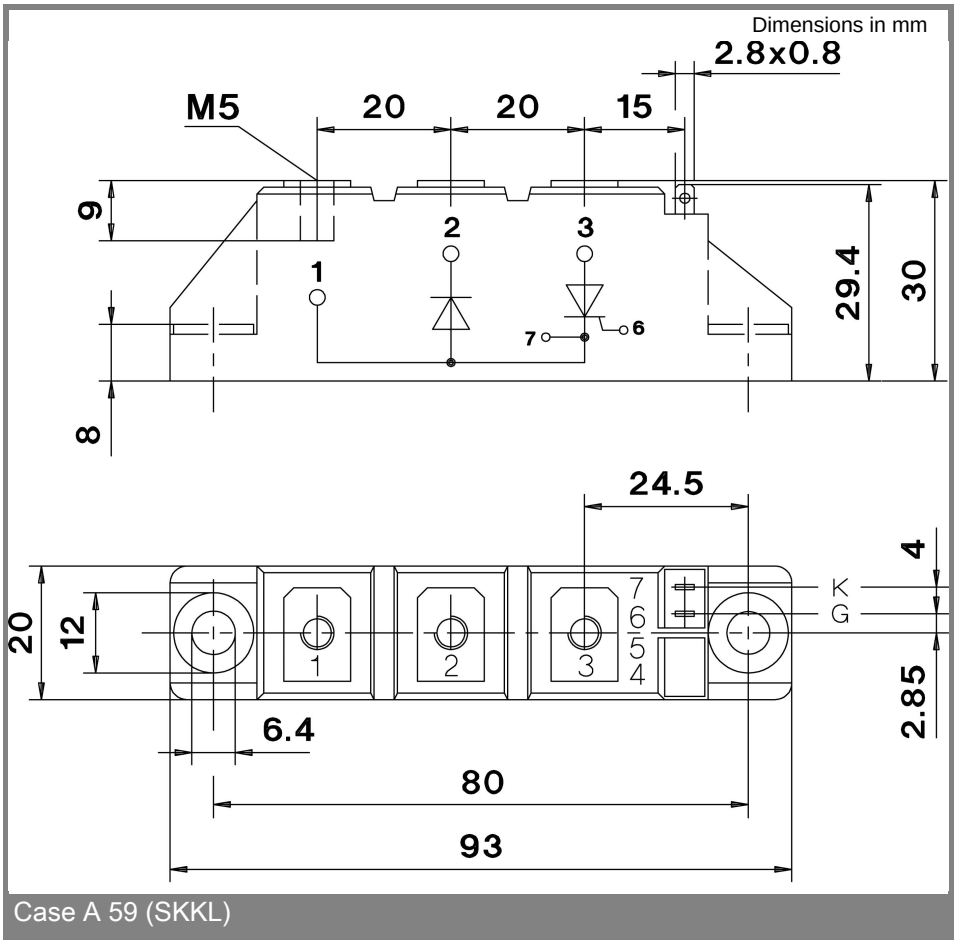
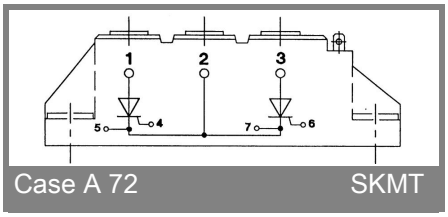


Fig. 8 Surge overload current vs. time

SKMT 92, SKKL 92



Case A 59 (SKKL)


Case A 72 SKMT

This technical information specifies semiconductor devices but promises no characteristics. No warranty or guarantee expressed or implied is made regarding delivery, performance or suitability.

